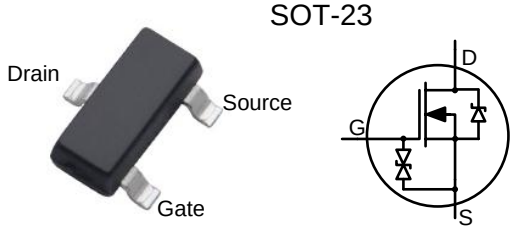
Depletion-Mode Power MOSFET

General Features

- ESD improved Capability
- Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- Halogen-free available

BV_{DSX}	$R_{DS(ON)}$ (Max.)	$I_{DSS,min}$
600V	700 Ω	5mA

SOT-23



Applications

- Normally-on Switches
- SMPS Start-up Circuit
- Linear Amplifier
- Converters
- Constant Current Source
- Telecom

Ordering Information

Part Number	Package	Marking	Remark
DMZ6005E	SOT-23	605E	Halogen Free

Absolute Maximum Ratings

T_A=25℃ unless otherwise specified

Symbol	Parameter	DMZ6005E	Unit
V_{DSX}	Drain-to-Source Voltage[1]	600	V
V_{DGX}	Drain-to-Gate Voltage[1]	600	V
I_D	Continuous Drain Current	0.02	A
I_{DM}	Pulsed Drain Current	0.08	
P_D	Power Dissipation	0.50	W
V_{GS}	Gate-to-Source Voltage	±20	V
$V_{ESD(G-S)}$	Gate Source ESD HBM, C=100pF, R=1.5k Ω	700	V
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	℃
T_J and T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	DMZ6005E	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	250	K/W

Electrical Characteristics

OFF Characteristics

T_A =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	600	--	--	V	V_{GS}=-5V, I_D=250μA
$I_{D(OFF)}$	Drain-to-Source Leakage Current	--	--	0.1	μA	V_{DS}=600V，V_{GS}= -5V
		--	--	10	μA	V_{DS}=600V，V_{GS}= -5V T_J=125℃
I_{GSS}	Gate-to-Source Leakage Current	--	--	20	uA	V_{GS}=+20V, V_{DS}=0V
		--	--	-20		V_{GS}=-20V, V_{DS}=0V

ON Characteristics

T_A =25℃ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_{DSS}	Saturated Drain-to-Source Current	5	--	25	mA	V_{GS}=0V, V_{DS}=25V
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	500	700	Ω	V_{GS}=0V，I_D=3mA [4]
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-3.0	--	-1.8	V	V_{DS} =3V, I_D=8μA
gfs	Forward Transconductance	--	15.4	--	mS	V_{DS} =10V, I_D=5mA

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance	--	12.3	--	pF	V_{GS}=-5V V_{DS}=25V f=1.0MHz
C_{OSS}	Oput Capacitance	--	2.6	--		
C_{RSS}	Reverse Transfer Capacitance	--	1.8	--		
Q_G	Total Gate Charge	--	1.55	--	nC	V_{GS}= -5V~5V V_{DS}=300V, I_D=7mA
Q_{GS}	Gate-to-Source Charge	--	0.12	--		
Q_{GD}	Gate-to-Drain (Miller) Charge	--	0.56	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	4	--	ns	V_{GS} = -5V~5V V_{DD} = 300V, I_D=7mA R_G = 20Ohm
t_{rise}	Rise Time	--	9	--		
$t_{d(OFF)}$	Turn-off Delay Time	--	14	--		
t_{fall}	Fall Time	--	84	--		

Source-Drain Diode Characteristics

T_A=25℃ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
V_{SD}	Diode Forward Voltage	--	--	1.2	V	I_{SD} =3.0 mA, V_{GS} = -10 V

NOTE：

[1] T_J=+25℃ to +150℃
[2] Repetitive rating, pulse width limited by maximum junction temperature.
[3] Pulse width≤380μs; duty cycle≤2%.

Figure 1. Maximum Power Dissipation vs. Case Temperature

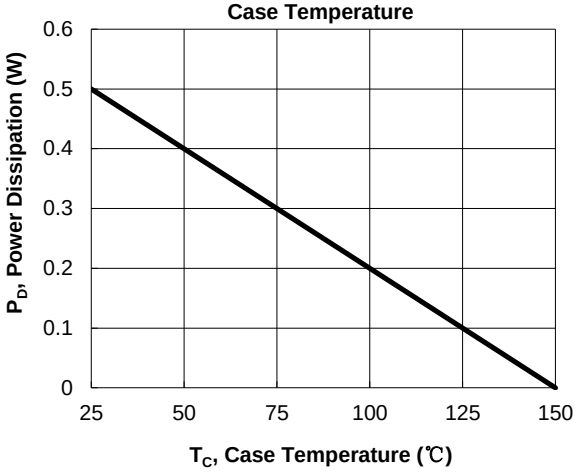


Figure 2. Maximum Continuous Drain Current vs Case Temperature

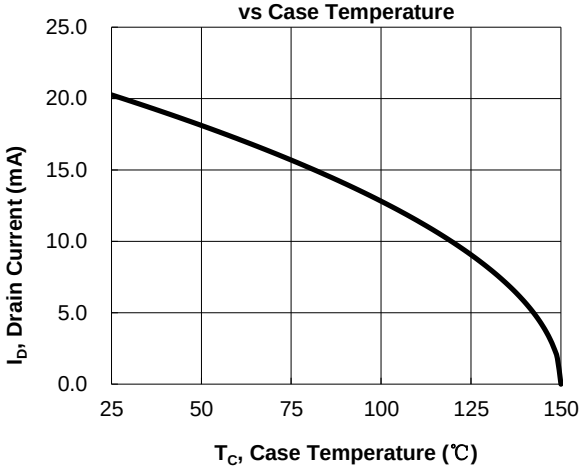


Figure 3. Typical Output Characteristics

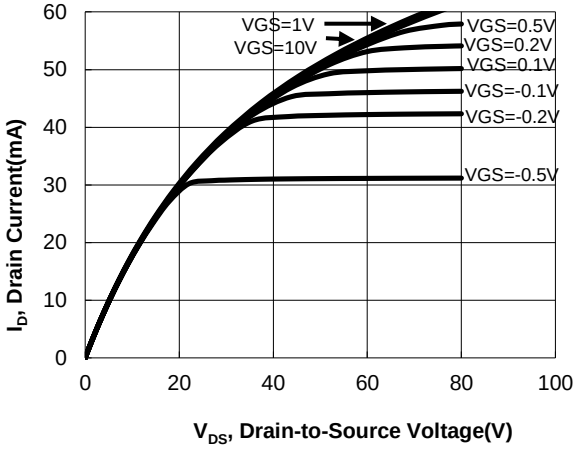


Figure 4. Typical Transfer Characteristics

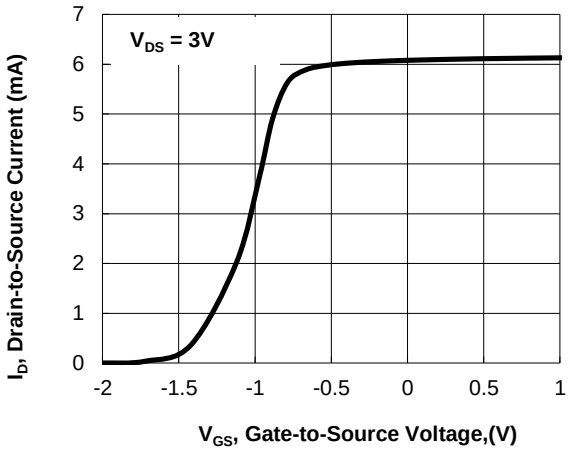


Figure 5. Typical Capacitance vs. Drain-to-Source Voltage

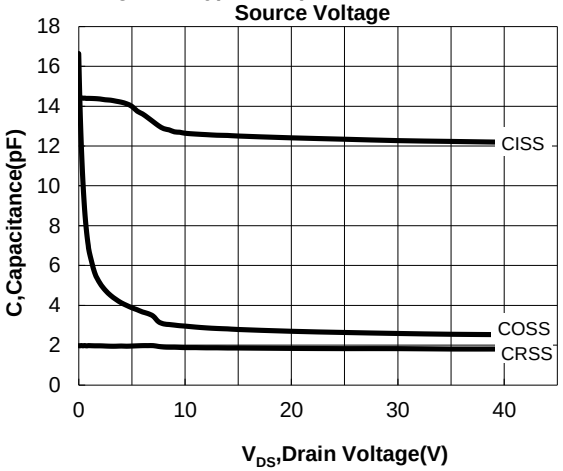
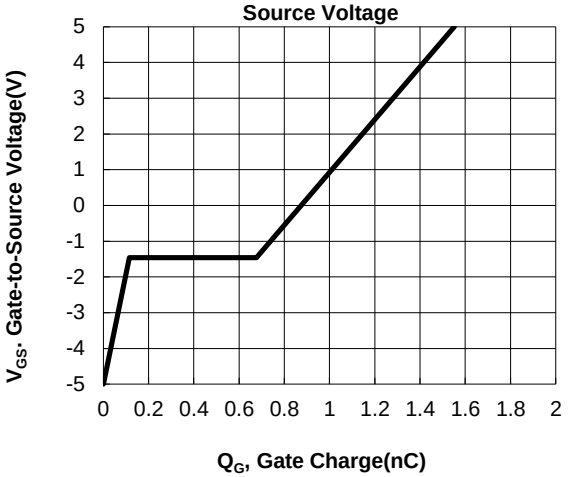
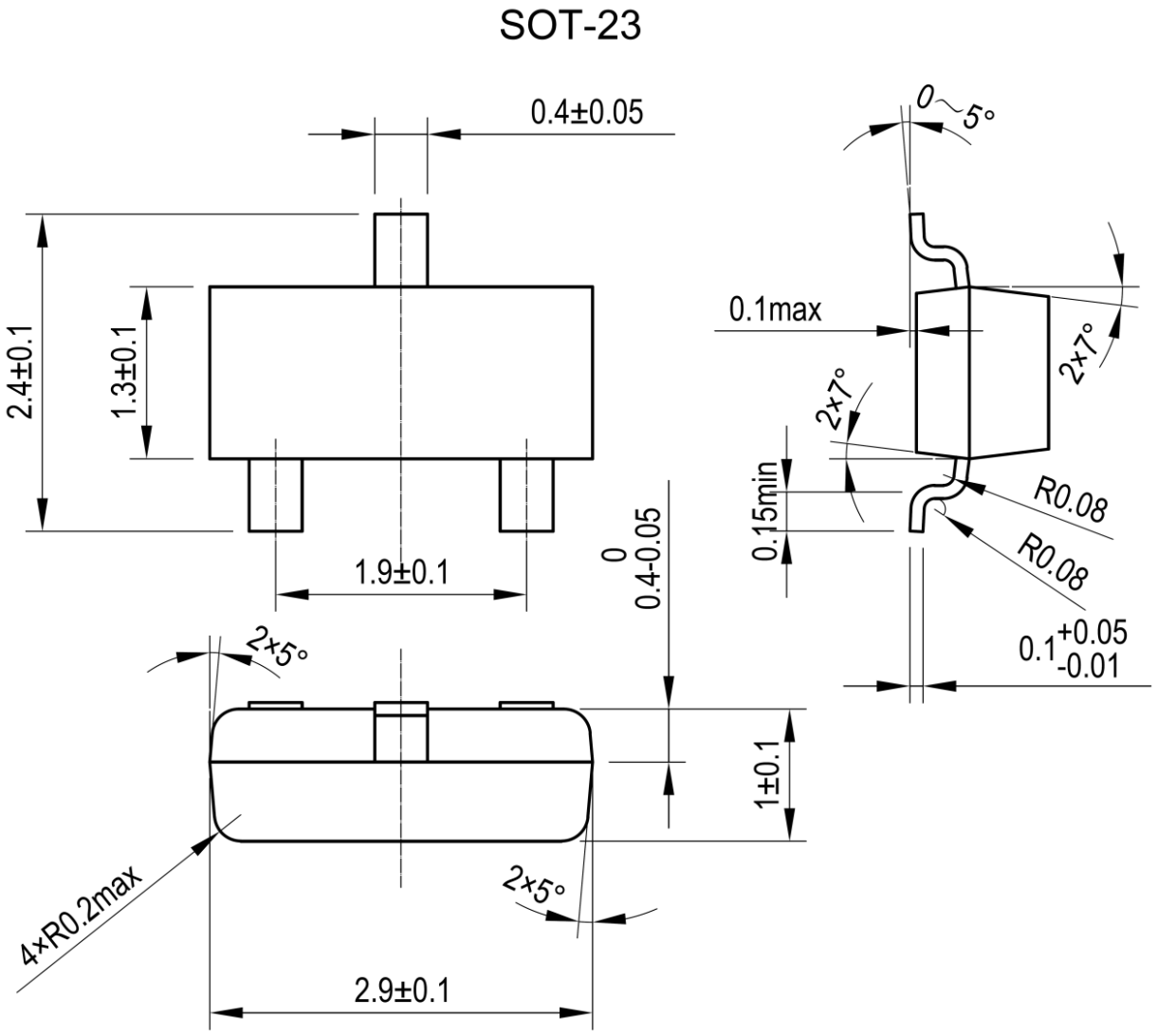


Figure 6. Typical Gate Charge vs. Gate-to-Source Voltage



Package Dimensions



Published by
DS Microelectronics Co., Ltd.
0512-50710709 www.ksmcu.com

Disclaimers

DS Microelectronics Co., Ltd. reserves the right to make change without notice in order to improve reliability, function or design and to discontinue any product or service without notice. Customers should obtain the latest relevant information before orders and should verify that such information is current and complete. All products are sold subject to DS Microelectronics Co., Ltd's terms and conditions supplied at the time of order acknowledgement.

DS Microelectronics Co., Ltd. warrants performance of its hardware products to the specifications at the time of sale, Testing, reliability and quality control are used to the extent DS Microelectronics Co., Ltd deems necessary to support this warrantee. Except where agreed upon by contractual agreement, testing of all parameters of each product is not necessary performed.

DS Microelectronics Co., Ltd. does not assume any liability arising from the use of any product or circuit designs described herein. Customers are responsible for their products and applications using DS Microelectronics Co., Ltd's components. To minimize risk, customers must provide adequate design and operating safeguards.

DS Microelectronics Co., Ltd. does not warrant or convey any license either expressed or implied under its patent rights, nor the rights of others. Reproduction of information in DS Microelectronics Co., Ltd's data sheets or data books is permissible only if reproduction is without modification or alteration. Reproduction of this information with any alteration is an unfair and deceptive business practice. DS Microelectronics Co., Ltd is not responsible or liable for such altered documentation.

Resale of DS Microelectronics Co., Ltd's products with statements different from or beyond the parameters stated by DS Microelectronics Co., Ltd. for the product or service voids all express or implied warrantees for the associated DS Microelectronics Co., Ltd's product or service and is unfair and deceptive business practice. DS Microelectronics Co., Ltd is not responsible or liable for any such statements.

Life Support Policy:

DS Microelectronics Co., Ltd's products are not authorized for use as critical components in life devices or systems without the expressed written approval of DS Microelectronics Co., Ltd.

As used herein:

1. Life support devices or systems are devices or systems which:
   a. are intended for surgical implant into the human body,
   b. support or sustain life,
   c. whose failure to perform when properly used in accordance with instructions for used provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.